N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
60V	7.5Ω @ V_{GS} = 5V	210mA

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

Features and Benefits

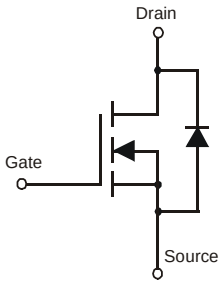
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Notes 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

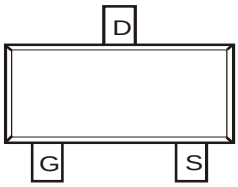
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

SOT23

Top View



Equivalent Circuit



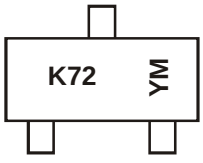
Top View

Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
2N7002-7-F	Standard	SOT23	3,000/Tape & Reel
2N7002-13-F	Standard	SOT23	10,000/Tape & Reel
2N7002Q-7-F	Automotive	SOT23	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K72 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2002	~	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	N	~	F	G	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$			V_{DGR}	60	V
Gate-Source Voltage		Continuous Pulsed	V_{GSS}	±20 ±40	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +85°C T_A = +100°C	I_D	170 120 105	mA
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +85°C T_A = +100°C	I_D	210 150 135	mA
Maximum Continuous Body Diode Forward Current (Note 7)		Pulsed Continuous	I_S	0.5 2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 6)	P_D	370	mW
	(Note 7)		540	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	348	°C/W
	(Note 7)		241	
Thermal Resistance, Junction to Case	(Note 7)	$R_{\theta JC}$	91	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	70	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current @ T_C = +25°C @ T_C = +125°C	I_{DSS}	—	—	1.0 500	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±10	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance @ T_J = +25°C	$R_{DS(ON)}$	—	3.2	7.5	Ω	V_{GS} = 5.0V, I_D = 0.05A
@ T_J = +25°C			—	5.0		V_{GS} = 10V, I_D = 0.5A
@ T_J = +125°C			4.4	13.5		V_{GS} = 10V, I_D = 0.5A
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance	g_{FS}	80	—	—	mS	V_{DS} =10V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	—	0.78	1.5	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	22	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.0	5.0	pF	
Gate Resistance	R_g	—	120	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	223	—	pC	V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	82	—		
Gate-Drain Charge	Q_{gd}	—	178	—		
SWITCHING CHARACTERISTICS (Note 9)						
Turn-On Delay Time	$t_{D(ON)}$	—	2.8	—	ns	V_{DD} = 30V, I_D = 0.2A, R_L = 150Ω, V_{GEN} = 10V, R_{GEN} = 25Ω
Turn-On Rise Time	t_R	—	3.0	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	7.6	—		
Turn-Off Fall Time	t_F	—	5.6	—		

Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

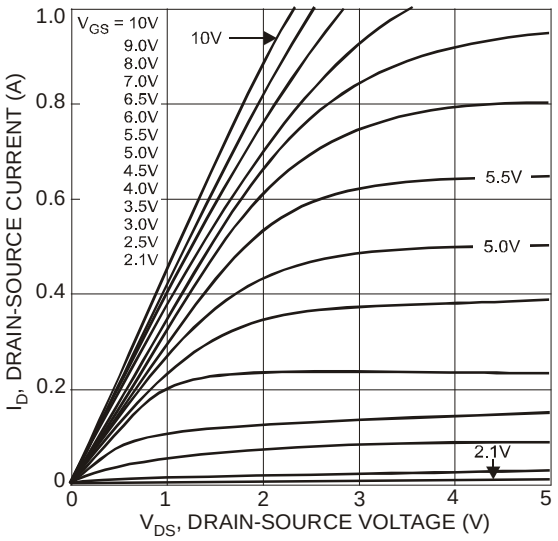


Fig. 1 On-Region Characteristics

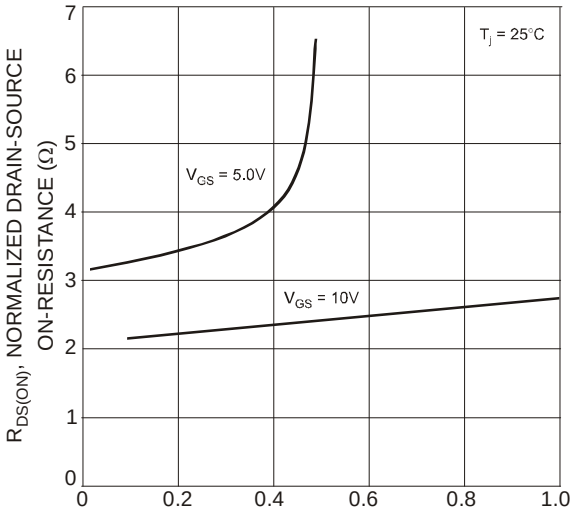


Fig. 2 On-Resistance vs. Drain Current

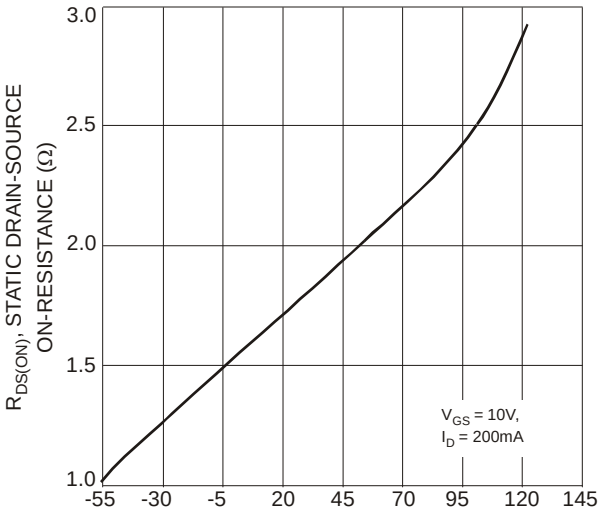


Fig. 3 On-Resistance vs. Junction Temperature

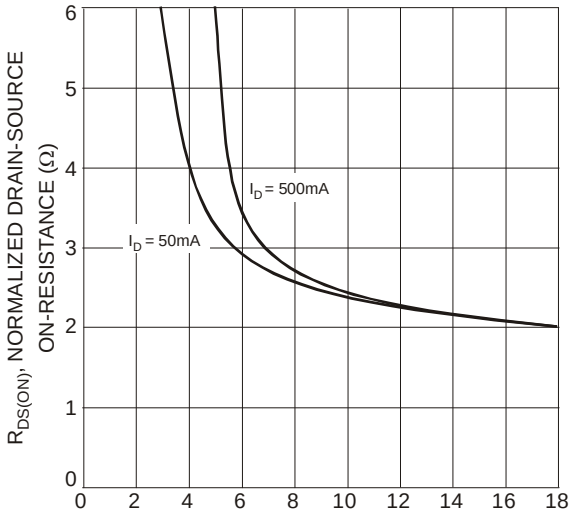


Fig. 4 On-Resistance vs. Gate-Source Voltage

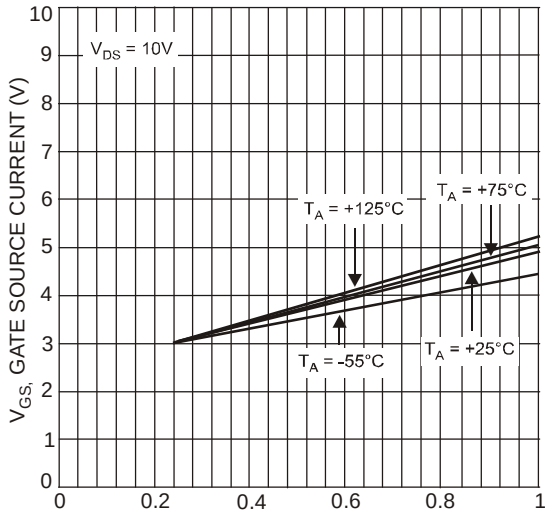


Fig. 5 Typical Transfer Characteristics

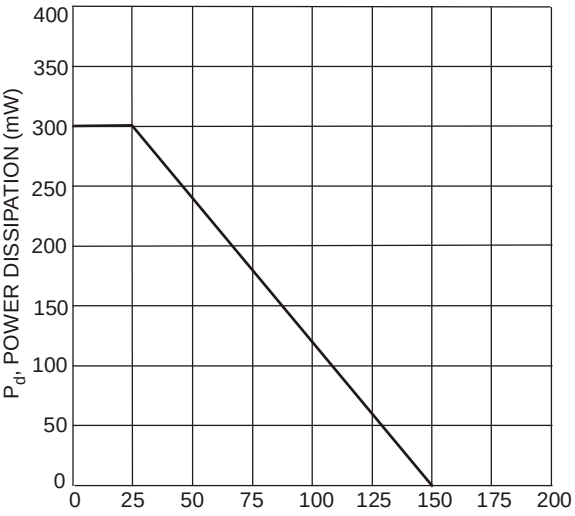


Fig. 6 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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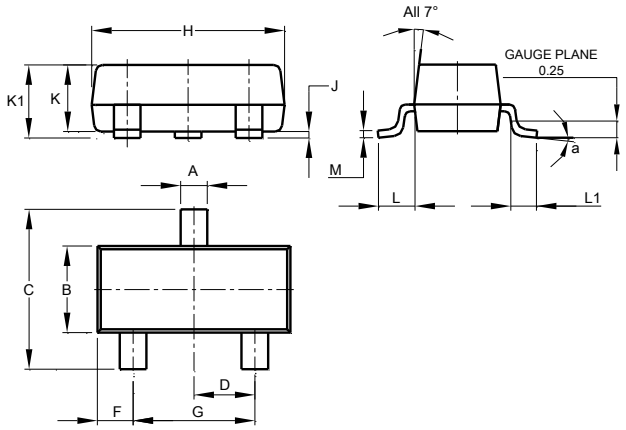
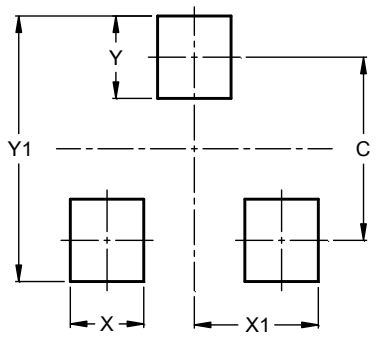


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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